

# IRSF3021 FULLY PROTECTED POWER MOSFET SWITCH

## IRSF3021

### Features

- Controlled Slew Rate Reduces EMI
- Over Temperature Protection with Auto-Restart
- Linear Current-Limit Protection
- Active Drain-to-Source Clamp
- ESD Protection
- Compatible with Standard Power MOSFET
- Low Operating Input Current
- Monolithic Construction
- Logic Level Input Threshold

$V_{ds}(clamp)$	50 V
$R_{ds}(on)$	200 m $\Omega$
$I_{lim}$	3.0 A
$T_{j}(sd)$	165°C
EAS	200 mJ

### Description

The IRSF3021 Lamp and DC Motor Driver is a fully protected three terminal monolithic SMART POWER MOSFET that features current limiting, over-temperature protection, gate-to-source ESD protection and gate-to-drain clamp for over-voltage protection.

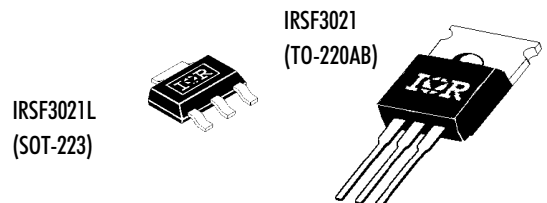
The on-chip protection circuit limits the drain current in the on-state. The over-temperature circuitry turns off the POWER MOSFET when the junction temperature exceeds 165°C. The device restarts automatically once it has cooled down below the reset temperature.

The IRSF3021 is specifically designed for driving loads that require overload protection and in-rush current control while operating in automotive and industrial environments. Targeted applications include resistive loads such as lamps or capacitive loads such as airbag squibs and DC motor drives.

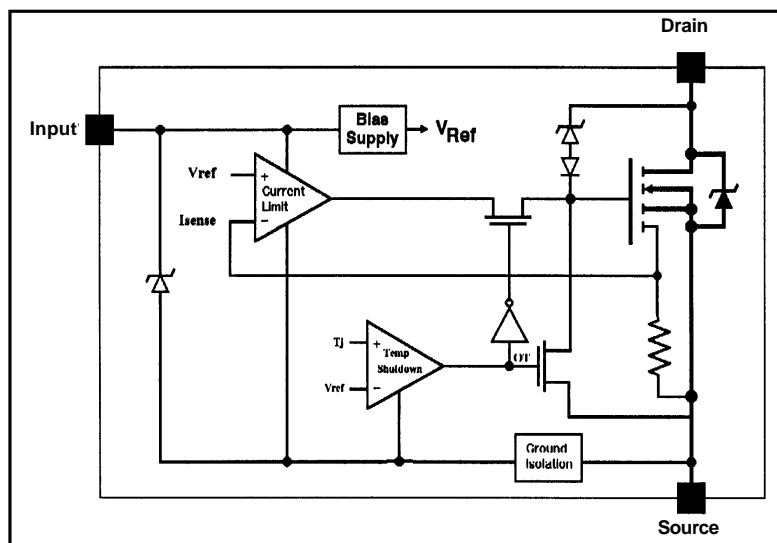
### Applications

- Cabin Lighting
- Airbag System
- Programmable Logic Controller
- DC Motor Drive

### Available Packages



### IRSF3021 Block Diagram



## Absolute Maximum Ratings

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. ( $T_c = 25^\circ\text{C}$  unless otherwise specified.)

		Minimum	Maximum	Units	Test Conditions
$V_{ds, \max}$	Continuous Drain to Source Voltage	—	50	V	
$V_{in, \max}$	Continuous Input Voltage	-0.3	8		
$I_{ds}$	Continuous Drain Current	—	self limited		
$P_d$	Power Dissipation	—	30	W	$T_c \leq 25^\circ\text{C}$
EAS	Unclamped Single Pulse Inductive Energy	—	200	mJ	
$V_{esd1}$	Electrostatic Discharge Voltage (Human Body Model)	—	4000	V	1000pF, 1.5k $\Omega$
$V_{esd2}$	Electrostatic Discharge Voltage (Machine Model)	—	1000		200pF, 0 $\Omega$
$T_{Jop}$	Operating Junction Temperature Range	-40	self-limited	$^\circ\text{C}$	
$T_{Stg}$	Storage Temperature Range	-40	175		
$T_L$	Lead Temperature (Soldering, 10 seconds)	—	300		

## Static Electrical Characteristics

( $T_c = 25^\circ\text{C}$  unless otherwise specified.)

		Minimum	Typical	Maximum	Units	Test Conditions
$V_{ds, \text{clamp}}$	Drain to Source Clamp Voltage	50	56	65	V	$I_{ds} = 6\text{A}$ , $t_p = 700\mu\text{s}$
$R_{ds(\text{on})}$	Drain to Source On Resistance	—	155	200	m $\Omega$	$V_{in} = 5\text{V}$ , $I_{ds} = 2\text{A}$
$I_{dss}$	Drain to Source Leakage Current	—	—	250	$\mu\text{A}$	$V_{ds} = 40\text{V}$ , $V_{in} = 0\text{V}$
$V_{th}$	Input Threshold Voltage	1.0	2.0	3.0	V	$V_{ds} = V_{in}$ , $I_{ds} + I_{in} = 10\text{mA}$
$I_{i, \text{on}}$	Input Supply Current (Normal Operation)	—	100	300	$\mu\text{A}$	$V_{in} = 5\text{V}$
$I_{i, \text{off}}$	Input Supply Current (Protection Mode)	—	500	—	$\mu\text{A}$	$V_{in} = 5\text{V}$
$V_{in, \text{clamp}}$	Input Clamp Voltage	9	10	—	V	$I_{in} = 1\text{mA}$
$V_{sd}$	Body-Drain Diode Forward Drop <sup>③</sup>	—	1.5	—	V	$I_{ds} = -2\text{A}$ , $R_{in} = 1\text{k}\Omega$

## Thermal Characteristics

		Minimum	Typical	Maximum	Units	Test Conditions
$R_{\theta jc}$	Junction to Case	—	—	4	$^\circ\text{C/W}$	TO-220AB
$R_{\theta jA}$	Junction to Ambient	—	—	60		
$R_{\theta jc}$	Junction to PCB	—	—	40	$^\circ\text{C/W}$	SOT-223
$R_{\theta jA}$	Junction to PCB <sup>①</sup>	—	—	60		

## Switching Electrical Characteristics

( $V_{CC} = 14\text{V}$ , Resistive Load ( $R_L$ ) = 10 $\Omega$ ,  $R_{in} = 100\Omega$ . Specifications measured at  $T_c = 25^\circ\text{C}$  unless otherwise specified.)

		Minimum	Typical	Maximum	Units	Test Conditions
$t_{don}$	Turn-On Delay Time	—	10	50	$\mu\text{s}$	$V_{in} = 0\text{V to } 5\text{V}$ , 50% to 90%
$t_r$	Rise Time	—	30	80		$V_{in} = 0\text{V to } 5\text{V}$ , 90% to 10%
$t_{doff}$	Turn-Off Delay Time	—	20	60		$V_{in} = 0\text{V to } 5\text{V}$ , 50% to 10%
$t_f$	Fall Time	—	15	50		$V_{in} = 0\text{V to } 5\text{V}$ , 10% to 90%
SR	Output Positive Slew Rate	-4	—	4	V/ $\mu\text{s}$	$V_{in} = 0\text{V to } 5\text{V}$ , +dVds/dt
SR	Output Positive Slew Rate	-4	—	4		$V_{in} = 0\text{V to } 5\text{V}$ , -dVds/dt

### Protection Characteristics

( $T_C = 25\text{ }^\circ\text{C}$  unless otherwise specified. Min/Max specifications are for  $T_C = -40\text{ }^\circ\text{C}$  to  $T_C = +125\text{ }^\circ\text{C}$  unless otherwise specified.)

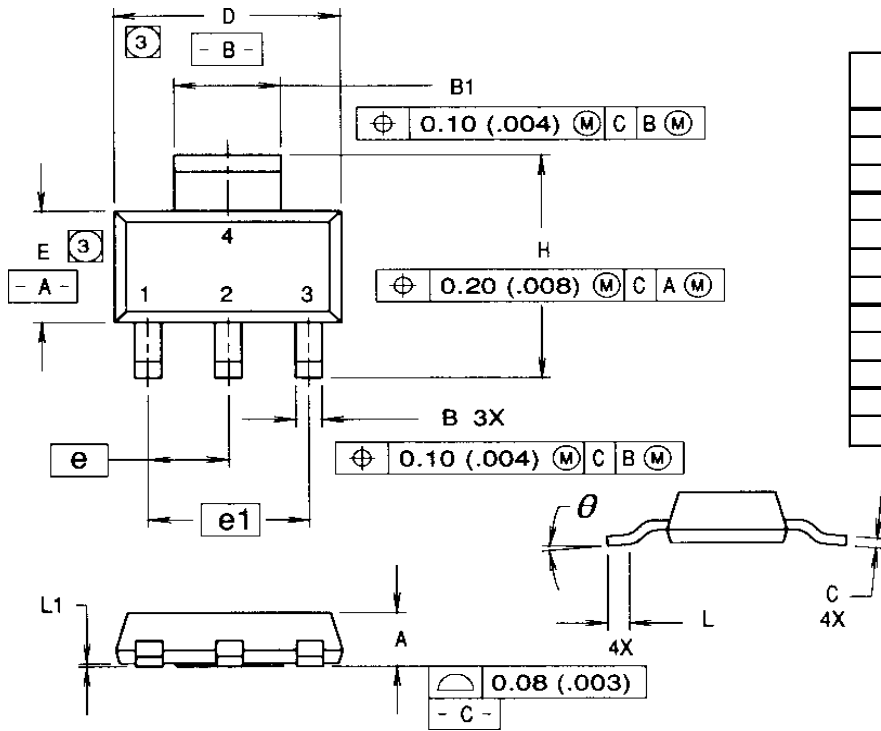
		Minimum	Typical	Maximum	Units	Test Conditions
$I_{ds(sd)}$	Current Limit	3.0	5.5	8.0	A	$V_{in} = 5V, V_{DS} = 14V$
$T_{j(sd)}$	Over Temperature Shutdown Threshold	155	165	—	$^\circ\text{C}$	$V_{in} = 5V, I_{ds} = 2A$
$V_{protect}$	Min. Input Voltage for Over-temp function	—	3	—	V	
$t_{Iresp}$	Current Limit Response Time	—	TBD	—	$\mu\text{s}$	
$I_{peak}$	Peak Short Circuit Current	—	10	—	A	
$t_{Tresp}$	Over-Temperature Response Time	—	TBD	—	$\mu\text{s}$	

#### Notes:

- ① When mounted on a 1" square PCB (FR-4 or G10 material). For recommended footprint and soldering techniques, refer to International Rectifier Application Note AN-994.
- ②  $E_{AS}$  is tested with a constant current source of 6A applied for 700 $\mu\text{s}$  with  $V_{in} = 0V$  and starting  $T_j = 25\text{ }^\circ\text{C}$ .
- ③ Input current must be limited to less than 5mA with a 1k $\Omega$  resistor in series with the input when the Body-Drain Diode is forward biased.

# IRSF3021

## Case Outline — SOT-223 (IRSF3021L)



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.55	1.80	0.061	0.071
B	0.65	0.85	0.026	0.033
B1	2.95	3.15	0.116	0.124
C	0.25	0.35	0.010	0.014
D	6.30	6.70	0.248	0.264
E	3.30	3.70	0.130	0.146
e	2.30 BSC		.0905 BSC	
e1	4.60 BSC		0.181 BSC	
H	6.71	7.29	0.287	0.264
L	—	0.91	—	0.036
L1	0.02	0.10	0.0006	0.004
$\theta$	10° MAX		10° MAX	

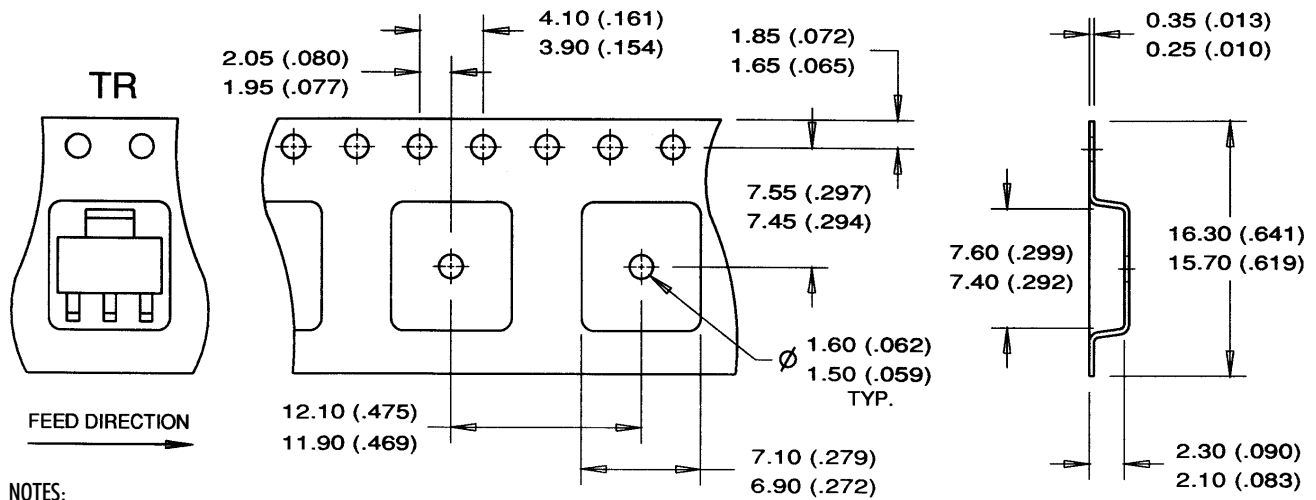
### NOTES:

1. Dimensioning and tolerancing per ANSI Y14.5M, 1982
2. Controlling dimension: INCH
3. Dimensions do not include lead flash
- ④ Conforms to JEDEC outline TO-261AA

### LEAD ASSIGNMENTS

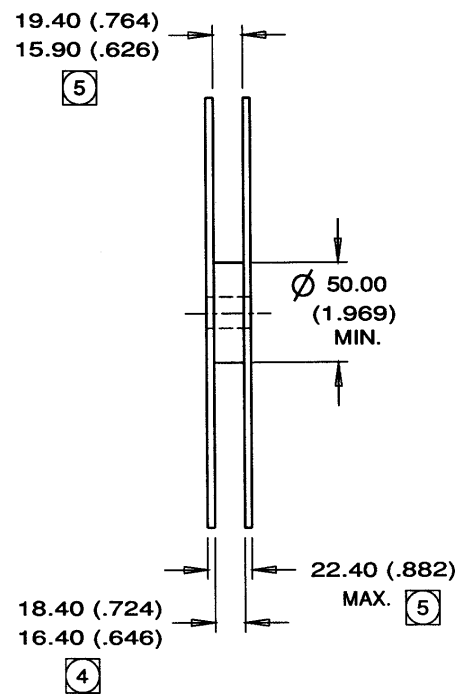
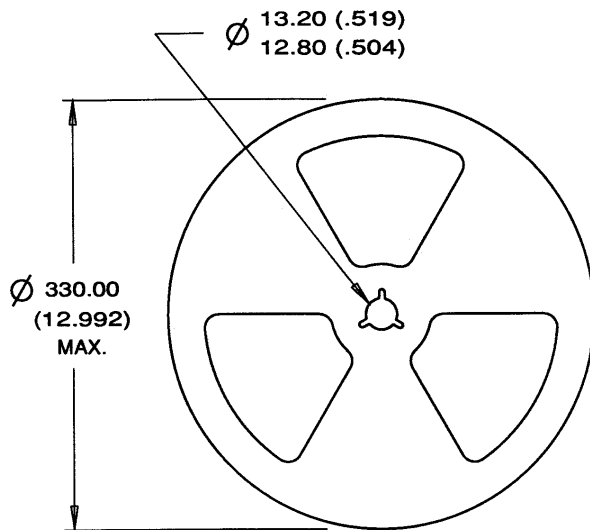
1. Gate
2. Drain
3. Source
4. Drain

**Tape and Reel — SOT-223 (IRSF3021L)**



**NOTES:**

1. Controlling dimension: MILLIMETER
2. Conforms to outline EIA-481 and EIA-541
3. Each  $\phi 330.00$  (13.00) reel contains 2,500 devices.

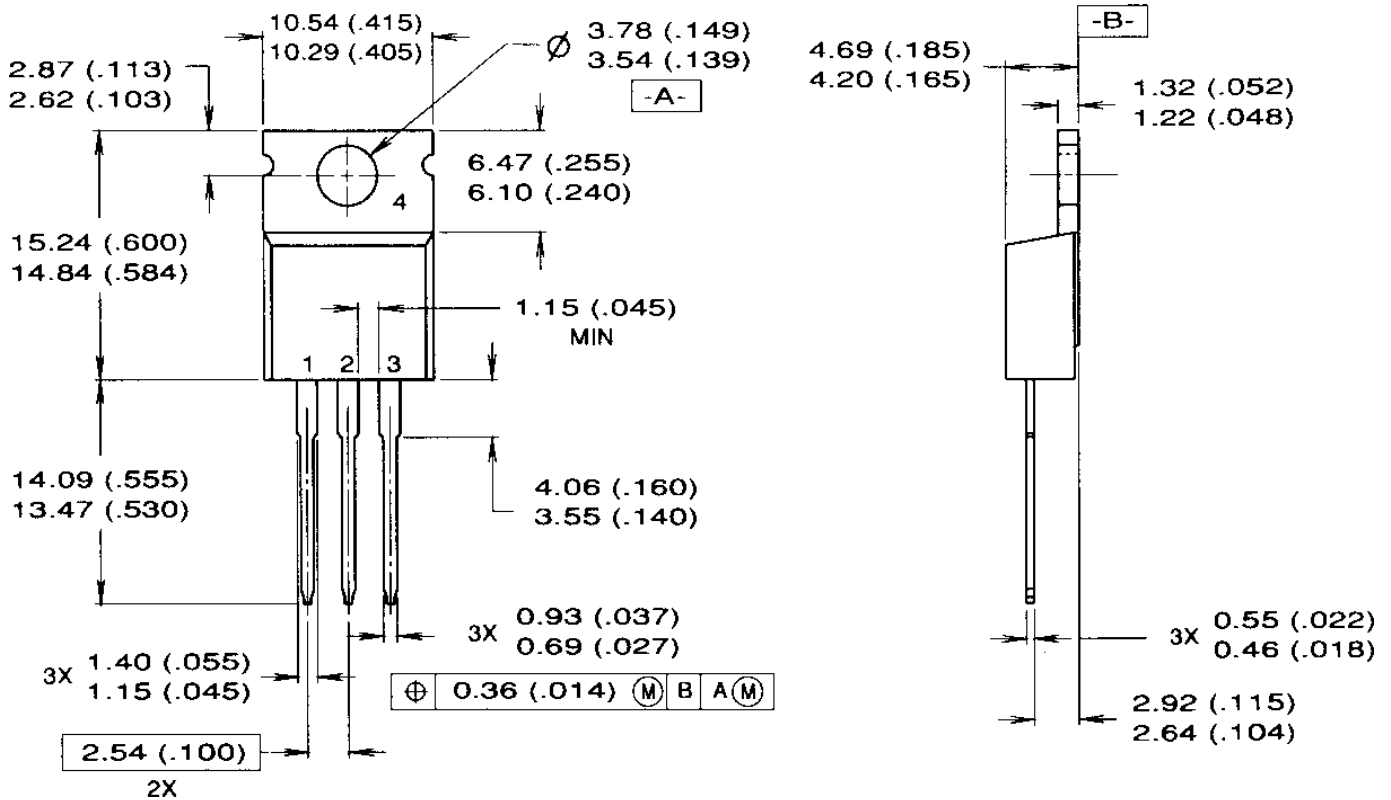


**NOTES:**

1. Controlling dimension: MILLIMETER
2. Conforms to outline EIA-481-1
- ③ Dimension measured at hub
- ④ Includes flange distortion at outer edge

# IRSF3021

## Case Outline — TO-220AB (IRSF3021)



### NOTES:

1. Dimensioning and tolerancing per ANSI Y14.5M, 1982
2. Controlling dimension: INCH
3. Dimensions shown are in millimeters (inches)
4. Conforms to JEDEC outline TO-251AA
5. Dimension does not include solder dip. Solder dip max. +0.16 (.006)

### LEAD ASSIGNMENTS

1. Gate
2. Drain
3. Source
4. Drain

International  
**IR** Rectifier

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Data and specifications subject to change without notice.

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